**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

## 3. Applications

- · Reverse battery protection
- Power management
- High-side load switch
- Motor drive

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-80	V
V <sub>GS</sub>	gate-source voltage		[1]	-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 25 °C		-	-	-35	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C		-	-	150	W
Static charac	cteristics		•	'			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -7 A; $T_j$ = 25 °C		-	42	55	mΩ

[1] See application note AN90001.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source	a	
4	G	gate		
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	\$ 017aaa094

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BUK6Y55-80P	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK6Y55-80P	6Y5580P

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# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-80	V
V <sub>GS</sub>	gate-source voltage		[1]	-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 25 °C		-	-35	Α
		V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 100 °C		-	-25	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-140	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C		-	150	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	-35	Α
I <sub>SM</sub>	peak source current	$T_{mb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-140	Α
ESD maximu	m rating		'			
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche ru	iggedness				'	'
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{sup} \le -80 \text{ V}; V_{GS} = -10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; I_D = -27.5 \text{ A}; unclamped$	[3]	-	72	mJ
		$V_{sup} \le -80 \text{ V}; V_{GS} = -10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; I_D = -6.3 \text{ A}; unclamped$	[3]	-	266	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$T_{j(init)} = 25  ^{\circ}C$	[3]	-	-27.5	A

<sup>1]</sup> See application note AN90001.

<sup>[2]</sup> Measured between all pins.

<sup>[3]</sup> Protected by 100% test.

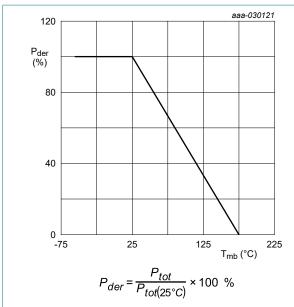


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

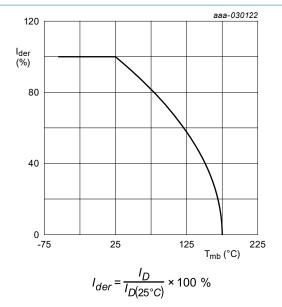


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

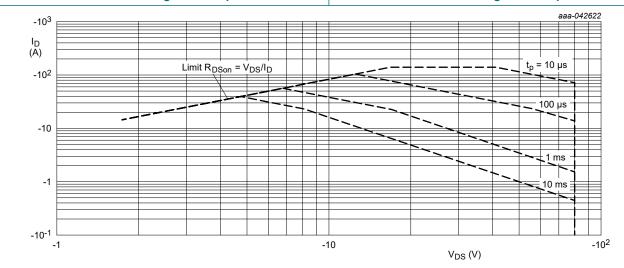


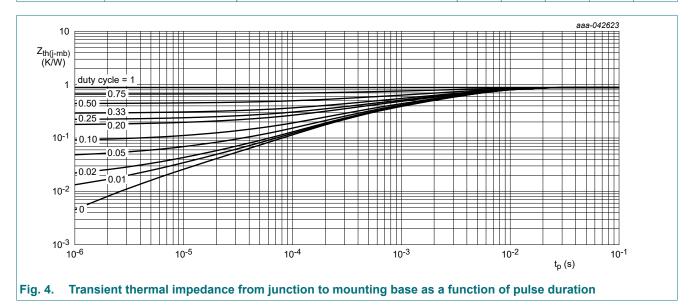
Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base		-	0.8	1	K/W



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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-80	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1.5	-2	-2.8	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		V <sub>DS</sub> = -80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	42	55	mΩ
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -7 A; T <sub>j</sub> = 175 °C	-	95	120	mΩ
		$V_{GS}$ = -6 V; $I_D$ = -6 A; $T_j$ = 25 °C	-	45	65	mΩ
		$V_{GS}$ = -4.5 V; $I_{D}$ = -4 A; $T_{j}$ = 25 °C	-	50	80	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -7 \text{ A}; T_j = 25 \text{ °C}$	-	3.2	-	S
$R_{G}$	gate resistance	f = 1 MHz	-	8.6	-	Ω
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -40 \text{ V}; I_D = -7 \text{ A}; V_{GS} = -10 \text{ V};$	-	40	60	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	6.8	-	nC
$Q_{GD}$	gate-drain charge		-	9.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -40 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2117	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	128	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	73	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -40 \text{ V}; I_D = -7 \text{ A}; V_{GS} = -10 \text{ V};$	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	76	-	ns
t <sub>f</sub>	fall time		-	288	-	ns
Source-dra	in diode		,	,	,	
V <sub>SD</sub>	source-drain voltage	$I_S = -6 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = -6 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	31	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = -40 V; T <sub>j</sub> = 25 °C	-	42	-	nC

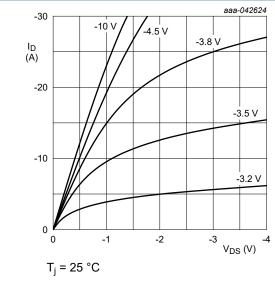


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

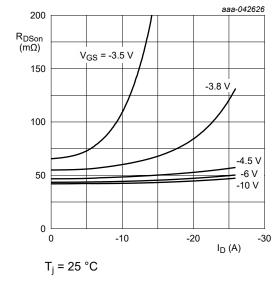


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

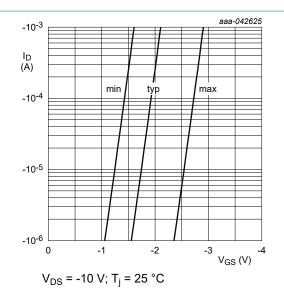


Fig. 6. Sub-threshold drain current as a function of gate-source voltage

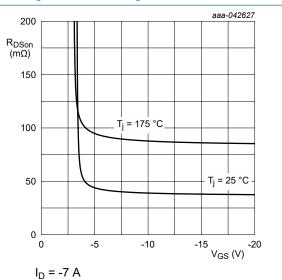


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

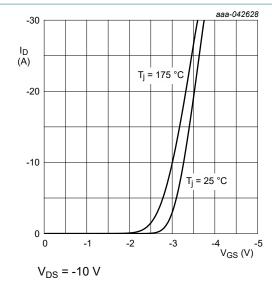


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

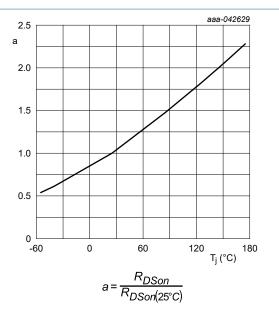


Fig. 10. Normalized drain-source on-state resistance as a function of junction temperature; typical values

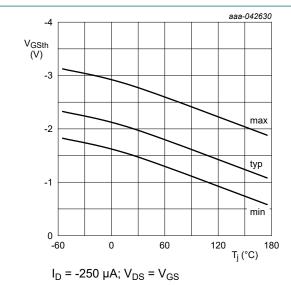


Fig. 11. Gate-source threshold voltage as a function of junction temperature

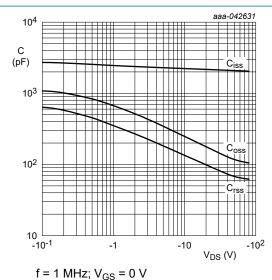


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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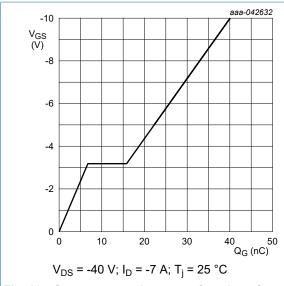


Fig. 13. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

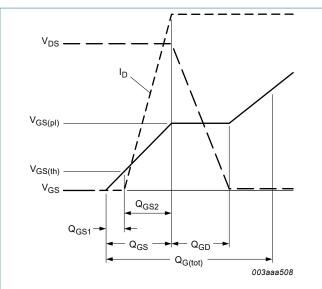


Fig. 14. Gate charge waveform definitions

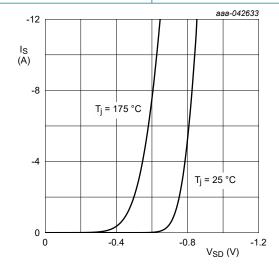
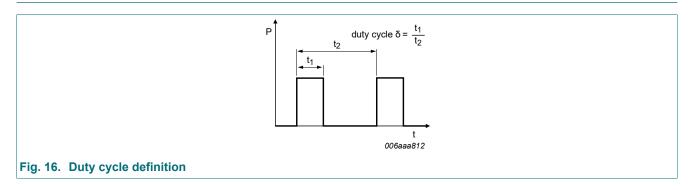


Fig. 15. Source current as a function of source-drain voltage; typical values

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## 11. Test information

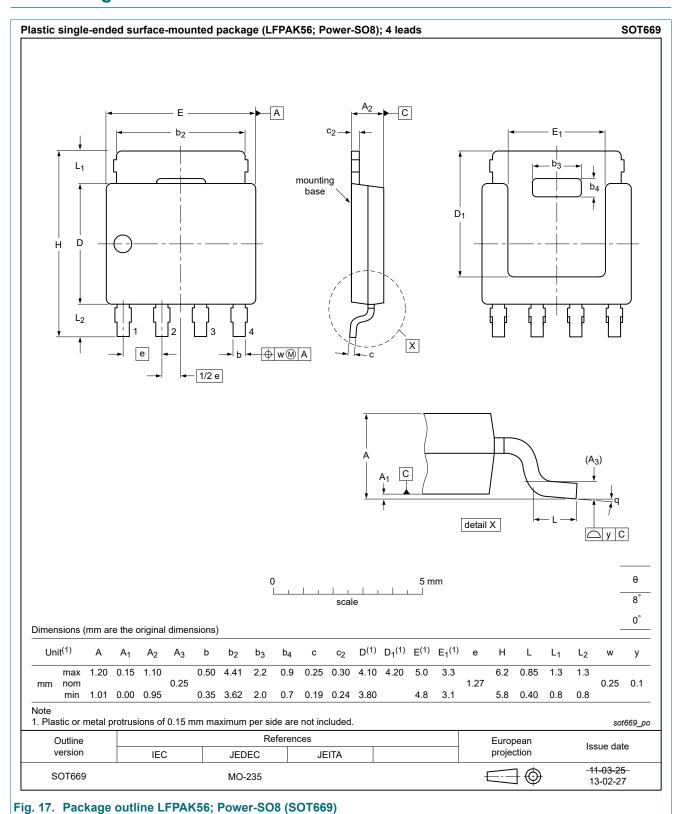


#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

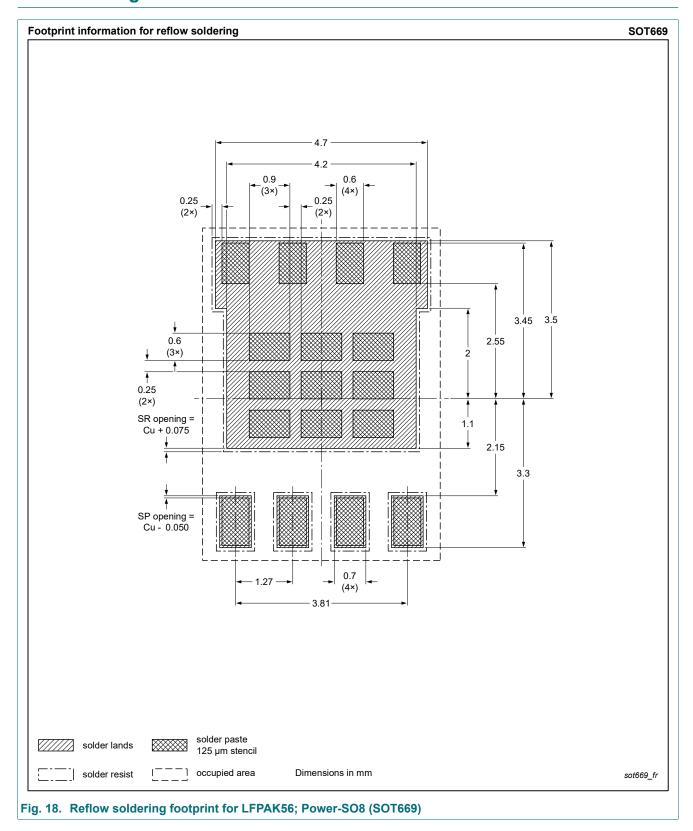
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# 12. Package outline



80 V, P-channel Trench MOSFET

# 13. Soldering



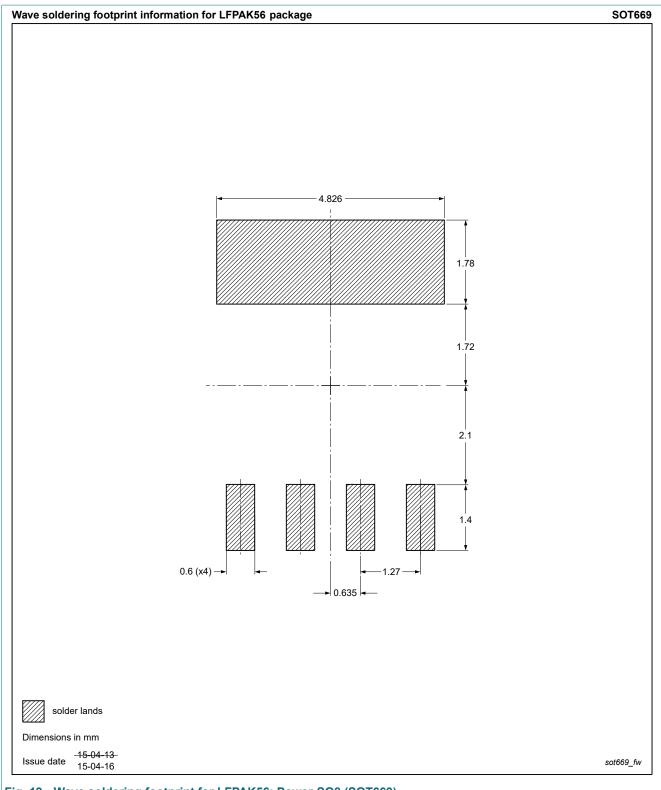


Fig. 19. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6Y55-80P v.1	20250508	Product data sheet	-	-

#### 80 V, P-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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